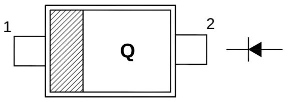
1SS413

SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

for high speed switching application

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**Q**"
Simplified outline SOD-523 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

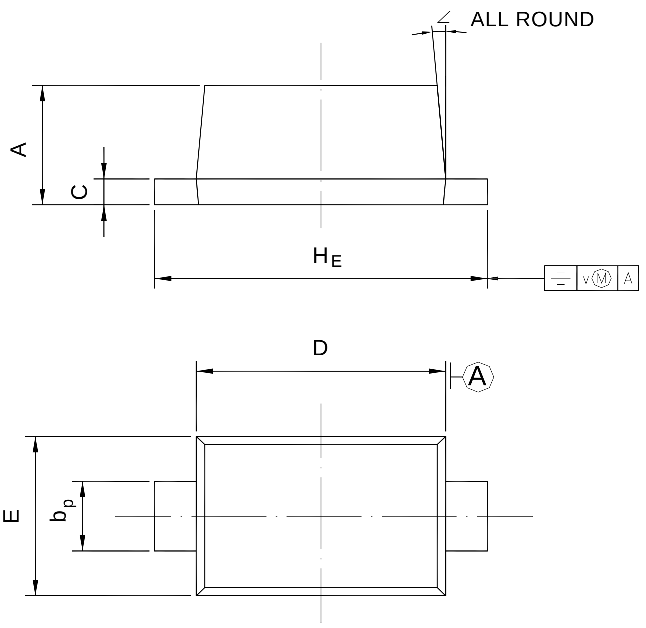
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	25	V
Reverse Voltage	V_R	20	V
Peak Forward Current	I_{FM}	100	mA
Average Forward Current	I_O	50	mA
Surge Current (10 ms)	I_{FSM}	1	A
Power Dissipation	P_{tot}	100	mW
Junction Temperature	T_J	125	°C
Storage Temperature	T_{stg}	- 55 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 50 mA	V_F	-	0.55	V
Reverse Current at V_R = 20 V	I_R	-	0.5	µA
Total Capacitance at V_R = 0 V, f = 1 MHz	C_T	3.9	-	pF

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-523**



UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°